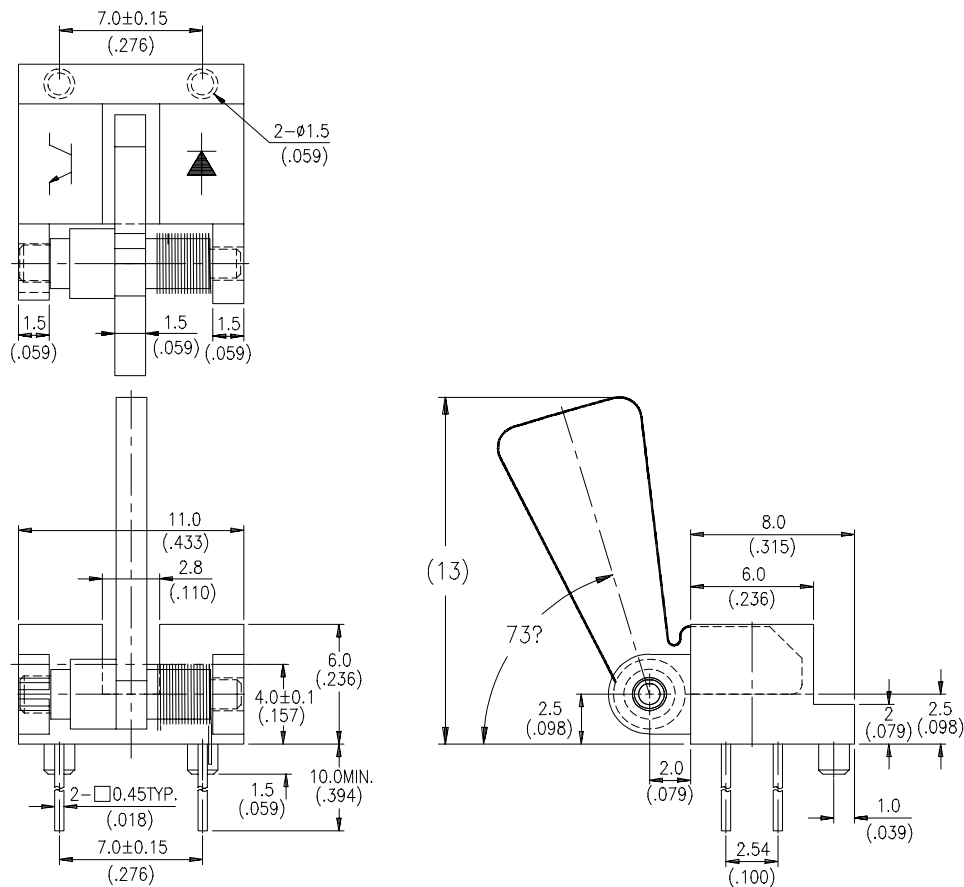


FEATURES

- * MECHANICAL SWITCH REPLACEMENT.
- * FOR DIRECT PC BOARD OR DUAL-IN-LINE SOCKET MOUNTING.
- * CUSTOMIZED LEVER ARM CAN BE DESIGNED FOR SPECIFIC APPLICATION.

PACKAGE DIMENSIONS



NOTES:

1. All dimensions are in millimeters (inches).
2. Tolerance is ± 0.25 mm (.010") unless otherwise noted.
3. Specifications are subject to change without notice.

**ABSOLUTE MAXIMUM RATINGS AT TA=25°C**

PARAMETER	MAXIMUM RATING	UNIT
IR Diode Continuous Forward Current	50	mA
IR Diode Reverse Voltage	5	V
Transistor Collector Currant	20	mA
Transistor Power Dissipation	75	mW(Note 1)
IR Diode Peak Forward Current (Pulse Wide = 10 μ S, 300 pps)	1	A
Diode Power Dissipation	60	mW(Note 1)
Phototransistor Collector-Emitter Voltage	30	V
Phototransistor Emitter-Collector Voltage	5	V
Operating Temperature Range	-25°C to + 85°C	
Storage Temperature Range	-55°C to + 100°C	
Lead Soldering Temperature [1.6mm (.063") Form Case]	260°C for 5 Seconds	

Note 1: Derate Linearly 1.33 mW/°C from 25°C



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ELECTRICAL OPTICAL CHARACTERISTICS AT TA=25°C

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
INPUT LED						
Forward Voltage	V _F		1.2	1.6	V	I _F = 20mA
Reverse Current	I _R			100	μ A	V _R =5V
OUTPUT PHOTOTRANSISTOR						
Collector-Emitter Breakdown Voltage	BV _{CEO}	30			V	I _C =1mA
Emitter-Collector Breakdown Voltage	BV _{ECO}	5			V	I _E =100 μ A
Collector-Emitter Dark Current	I _{CEO}			100	nA	V _{CE} =10V
COUPLER						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}			0.4	V	I _C =0.25mA I _F =20mA
On State Collector Current	I _{C(ON)}	0.5			mA	V _{CE} =5V I _F =20mA

TYPICAL ELECTRICAL / OPTICAL CHARACTERISTICS CURVES

(25°C Ambient Temperature Unless Otherwise Noted)

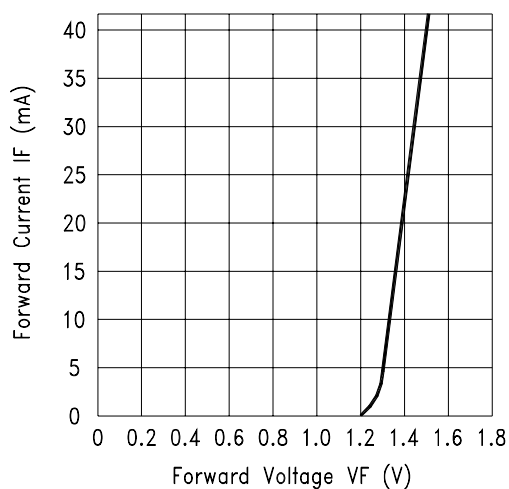


Fig.1 FORWARD CURRENT VS. FORWARD VOLTAGE

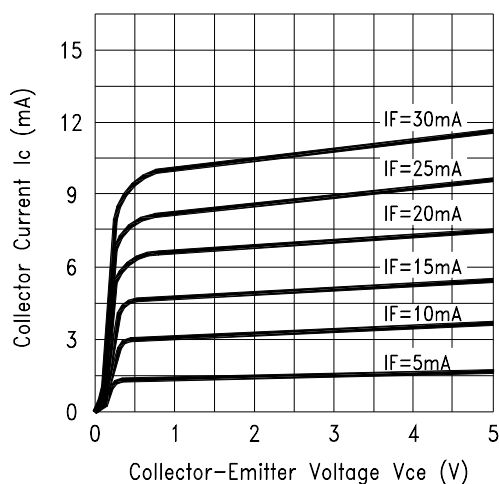


Fig.2 COLLECTOR CURRENT VS. COLLECTOR VOLTAGE

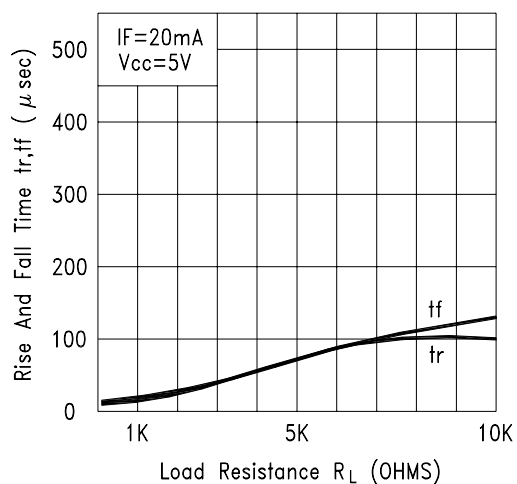


Fig.3 RISE AND FALL TIME VS. LOAD RESISTANCE

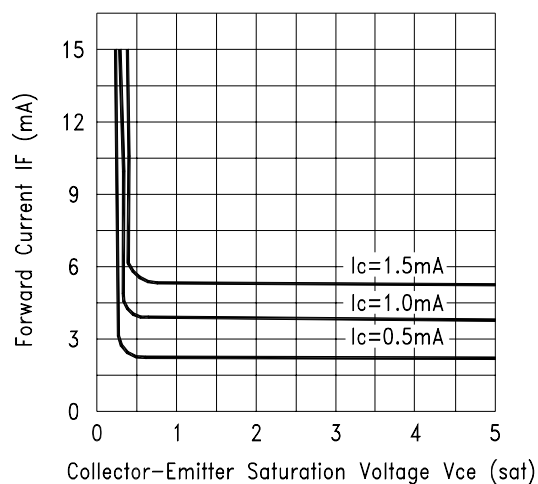


Fig.4 FORWARD CURRENT VS. Collector-Emitter Saturation Voltage